



Material Composition Declaration

EPC2367

Company Name	Efficient Power Conversion (EPC)	Issue Date:	7/21/2025
Contact Name:	Yanping Ma	Contact Title:	VP Quality
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Part Weight:	20.3 mg	Type of Product:	eGaN FET in FCQFN package

Construction Element	Substance	CAS No. If Applicable	Weight	Mass	Sum	Mass
			(mg)	(%)	(%)	(ppm)
Chip	Silicon	7440-21-3	6.9550	34.3091	35.5648	343091
	Silicon oxide	7631-86-9	0.0429	0.2115		2115
	Silicon nitride	12033-89-5	0.0307	0.1513		1513
	Gallium nitride	25617-97-4	0.0322	0.1587		1587
	Aluminum	7429-90-5	0.0002	0.0012		12
	Aluminum nitride	24304-00-5	0.0059	0.0291		291
	Titanium	7440-32-6	0.0023	0.0111		111
	Titanium nitride	25583-20-4	0.0385	0.1899		1899
	Copper	7440-50-8	0.0000	0.0000		0
	Tungsten	7440-33-7	0.0171	0.0846		846
	Polyimide		0.0848	0.4183	4183	
Under Bump Metal	Titanium	7440-32-6	0.0006	0.0027	0.0297	27
	Copper	7440-50-8	0.0055	0.0270		270
Solder Bump	Copper	7440-50-8	0.6790	3.3495	4.3810	33495
	Nickel	7440-02-0	0.0327	0.1611		1611
	Tin	7440-31-5	0.1733	0.8547		8547
	Silver	7440-22-4	0.0032	0.0157		157
Package	Copper	7440-50-8	5.6981	28.1087	60.0245	281087
	Mold Compound		6.3348	31.2497		312497
	Nickel	7440-02-0	0.1328	0.6552		6552
	Palladium	7440-05-3	0.0012	0.0060		60
	Potassium Gold Gyanide	13967-50-5	0.0010	0.0050		50
Sum in total:			20.2716	100.0000	100.0000	1000000

Note:

The substance content disclosed herewith is approximate and is based on engineering calculation. Statements are based on our present knowledge and may subject to change at any time due to technical requirements and development. EPC may update this document without notification. Statement may not include information regarding the minute quantities of dopant and metal materials in the electrical devices contained within the finished product.